

Preliminary Information

Low rDS(on) Small-Signal MOSFETs TMOS P-Channel High Side Driver

Part of the GreenLine $^{\text{\tiny M}}$ Portfolio of devices with energy-conserving traits.

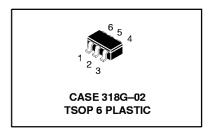
These miniature surface mount MOSFETs utilize Motorola's High Cell Density, HDTMOS™ process. Low rDS(on) assures minimal power loss and conserves energy, making this device ideal for use in small power management circuitry. Typical applications are switching small loads for power management in portable and battery–powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

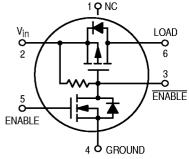
- Low rDS(on) Provides Higher Efficiency and Extends Battery Life
- Miniature 6-Lead TSOP 6 Surface Mount Package Saves Board Space
- Provides High Side Switching Capability Enabled by a High Impedance Logic Level Input

MGICP020

Motorola Preferred Device

P-CHANNEL ENHANCEMENT-MODE HIGH SIDE SWITCH $^{\rm rDS(on)} = 0.9~\Omega$ (TYP)





MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Maximum V _{CC} Voltage	Vcc	20	Vdc
Enable Voltage — Continuous	V _{enable}	± 20	Vdc
Load Current — Continuous @ T _A = 25°C — Pulsed Load Current (t _p ≤ 10 μs)	l _{load} l _{load}	300 750	mAdc
Total Power Dissipation @ T _A = 25°C (derate linearly to 0 mW @ +150°C)	PD	345	mW
Operating and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C
Thermal Resistance — Junction-to-Ambient	R ₀ JA	360	°C/W
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	TL	260	°C

ORDERING INFORMATION

Device	Reel Size	Tape Width	Quantity
MGICP020T1	7	8 mm embossed tape	3000
MGICP020T3	13	8 mm embossed tape	10,000

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HDTMOS is a trademark of Motorola, Inc. TMOS is a registered trademark of Motorola, Inc.

Thermal Clad is a trademark of the Bergquist Company.

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Preferred devices are Motorola recommended choices for future use and best overall value.



MGICP020

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Chara	Symbol	Min	Тур	Max	Unit	
OFF CHARACTERISTICS						
Blocking Voltage (Venable = 0 Vdc, I _{load} = 10 μA)		V _(Block)	20	_	_	Vdc
Zero Gate Voltage Drain Current (VCC = 20 Vdc, V _{enable} = 0 Vdc) (VCC = 20 Vdc, V _{enable} = 0.8 Vdc)		l(Leak)	_	_	1.0 10	μAdc
Enable Leakage Current (Venable = ±	20 Vdc, V _{CC} = 0)	Enable	_	<u> </u>	±100	nAdc
ON CHARACTERISTICS (1)						•
Enable Threshold Voltage (V _{CC} = 4.5 Vdc, I _{load} = 250 μAdc)		V _{enable(th)}	1.0	1.7	2.2	Vdc
Static On-Resistance (V _{CC} = 4.5 Vdc, I _{load} = 100 mA, V _{enable} = 3.0 Vdc)		R _(on)	_	0.9	1.25	Ohms
DYNAMIC CHARACTERISTICS						
Input Capacitance	$(V_{CC} = 5.0 \text{ V})$	C _{iss}	_	16	_	pF
Output Capacitance	(V _{CC} = 5.0 V)	C _{oss}	_	18	_	1
Transfer Capacitance	(V _{enable} = 3.0 V)	C _{rss}	_	120	_	1
SWITCHING CHARACTERISTICS (2)						
Turn-On Delay Time		[†] d(on)	_	10	_	ns
Rise Time	(V _{DD} = 15 Vdc, I _D = 0.7 A,	t _r	_	60	_	1
Turn-Off Delay Time	$R_L = 20 \Omega$)	^t d(off)	_	240	_	μs
Fall Time		tf	_	100	_	1
NPUT-LOAD DIODE CHARACTERIS	rics			•		
Continuous Current		ls	_	-	0.3	Α
Pulsed Current (1)		ISM	_	<u> </u>	0.75	1
Forward Voltage	I _{SD} = 100 mA	V _{SD}	_	0.75	_	V

⁽¹⁾ Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
(2) Switching characteristics are independent of operating junction temperature.

TYPICAL CHARACTERISTICS

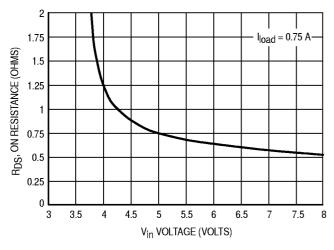


Figure 1. On Resistance versus Supply Voltage

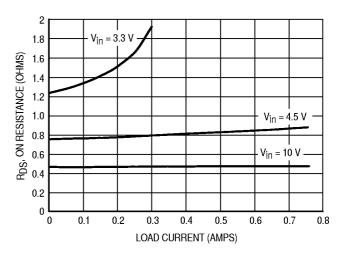


Figure 2. On Resistance versus Load Current

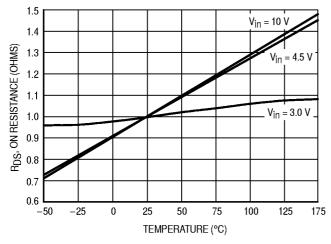


Figure 3. On-Resistance versus Temperature

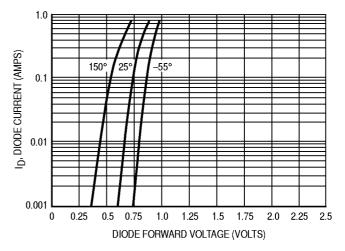
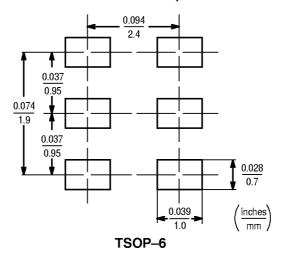


Figure 4. Body Diode Forward Voltage

INFORMATION FOR USING THE TSOP-6 SURFACE MOUNT PACKAGE

MINIMUM RECOMMENDED FOOTPRINT FOR SURFACE MOUNTED APPLICATIONS

Surface mount board layout is a critical portion of the total design. The footprint for the semiconductor packages must be the correct size to insure proper solder connection interface between the board and the package. With the correct pad geometry, the packages will self align when subjected to a solder reflow process.



TSOP-6 POWER DISSIPATION

The power dissipation of the TSOP–6 is a function of the drain pad size. This can vary from the minimum pad size for soldering to a pad size given for maximum power dissipation. Power dissipation for a surface mount device is determined by $T_{J(max)}$, the maximum rated junction temperature of the die, $R_{\theta JA}$, the thermal resistance from the device junction to ambient, and the operating temperature, T_A . Using the values provided on the data sheet for the TSOP–6 package, P_D can be calculated as follows:

$$P_D = \frac{T_{J(max)} - T_A}{R_{\theta JA}}$$

The values for the equation are found in the maximum ratings table on the data sheet. Substituting these values into the equation for an ambient temperature T_A of 25°C, one can calculate the power dissipation of the device which in this case is 275 milliwatts.

$$P_D = \frac{150^{\circ}C - 25^{\circ}C}{400^{\circ}C/W} = 275 \text{ milliwatts}$$

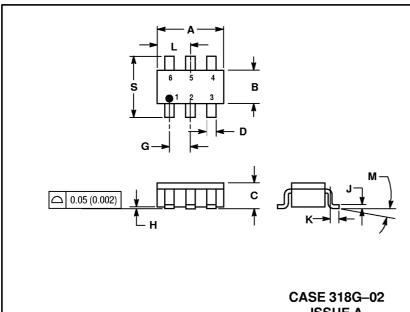
The 400°C/W for the TSOP–6 package assumes the use of the recommended footprint on a glass epoxy printed circuit board to achieve a power dissipation of 950 milliwatts. There are other alternatives to achieving higher power dissipation from the TSOP–6 package. Another alternative would be to use a ceramic substrate or an aluminum core board such as Thermal Clad™. Using a board material such as Thermal Clad, an aluminum core board, the power dissipation can be doubled using the same footprint.

SOLDERING PRECAUTIONS

The melting temperature of solder is higher than the rated temperature of the device. When the entire device is heated to a high temperature, failure to complete soldering within a short time could result in device failure. Therefore, the following items should always be observed in order to minimize the thermal stress to which the devices are subjected.

- Always preheat the device.
- The delta temperature between the preheat and soldering should be 100°C or less.*
- When preheating and soldering, the temperature of the leads and the case must not exceed the maximum temperature ratings as shown on the data sheet. When using infrared heating with the reflow soldering method, the difference shall be a maximum of 10°C.
- The soldering temperature and time shall not exceed 260°C for more than 10 seconds.
- When shifting from preheating to soldering, the maximum temperature gradient shall be 5°C or less.
- After soldering has been completed, the device should be allowed to cool naturally for at least three minutes.
 Gradual cooling should be used as the use of forced cooling will increase the temperature gradient and result in latent failure due to mechanical stress.
- Mechanical stress or shock should not be applied during cooling.
- * Soldering a device without preheating can cause excessive thermal shock and stress which can result in damage to the device.

PACKAGE DIMENSIONS



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
Α	2.90	3.10	0.1142	0.1220
В	1.30	1.70	0.0512	0.0669
С	0.90	1.10	0.0354	0.0433
D	0.25	0.50	0.0098	0.0197
G	0.85	1.05	0.0335	0.0413
Н	0.013	0.100	0.0005	0.0040
J	0.10	0.26	0.0040	0.0102
K	0.20	0.60	0.0079	0.0236
Г	1.25	1.55	0.0493	0.0610
М	0°	10°	0 °	10°
S	2.50	3.00	0.0985	0.1181

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